

1 ABSTRACT OF THE DISCLOSURE

2 The invention includes a method of forming a semiconductor
3 construction. A first substrate is provided which comprises silicon-
4 containing structures separated from one another by an insulative
5 material. The silicon-containing structures define an upper surface. A
6 second semiconductor substrate is provided which comprises a
7 monocrystalline material having a damage region therein. The second
8 semiconductor substrate is bonded to the silicon-containing structures of
9 the first substrate at the upper surface. The monocrystalline material
10 is then cleaved along the damage region. The invention also
11 encompasses a semiconductor construction comprising a first substrate
12 having silicon-containing structures separated from one another by an
13 insulative material, and a second substrate comprising a monocrystalline
14 material. The silicon-containing structures of the first substrate define
15 an upper surface, and the monocrystalline material of the second
16 substrate is bonded over the silicon-containing structures at the upper
17 surface.

18
19
20
21
22
23